



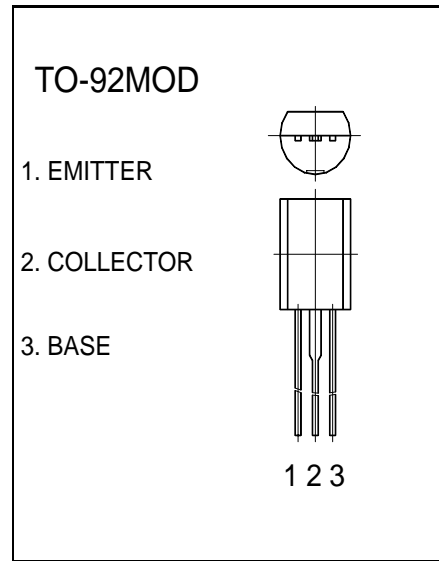
2SC1627A TRANSISTOR (NPN)

FEATURE

- z Complementary to 2SA817A
- z Driver Stage Application of 30 to 35 Watts Amplifiers

MAXIMUM RATINGS(T_A=25 / unless otherwise noted)

Symbol	parameter	Value	Units
V _{CBO}	Collector-Base Voltage	80	V
V _{CEO}	Collector-Emitter Voltage	80	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	0.4	A
P _C	Collector Power Dissipation	0.8	W
T _j	Junction Temperature	150	/
T _{stg}	Storage Temperature Range	-55-150	/



ELECTRICAL CHARACTERISTICS (T_{amb}=25 / unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100 μA, I _E =0	80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =5mA, I _B =0	80			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100 μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =50V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =2 V, I _C = 50mA	70		240	
	h _{FE(2)}	V _{CE} =2 V, I _C = 200mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 200mA, I _B = 20mA			0.4	V
Base-emitter voltage	V _{BE(on)}	V _{CE} = 2V, I _C = 5mA	0.55		0.8	V
Transition frequency	f _T	V _{CE} = 10 V, I _C = 10mA		100		MHz

CLASSIFICATION OF h_{FE(1)}

Rank	O	Y
Range	70-140	120-240